



2SD1270

PNP EPITAXIAL SILICON TRANSISTOR

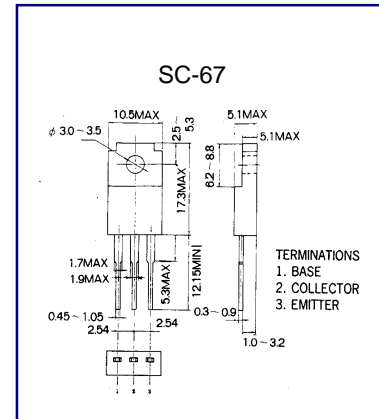
POWER AMPLIFIER

VERTICAL DEFLECTION OUTPUT

- Complement to 2SB945

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-130	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base voltage	V _{EB0}	-5	V
Collector Current (DC)	I _C	-5	A
Collector Dissipation ($T_c=25^\circ\text{C}$)	P _C	40	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = -150V , I _E =0			-10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V , I _C =0			-10	μA
DC Current Gain	h _{FE1}	V _{CE} = -2.0V , I _C =-2.0A	60		260	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =-4A , I _B =-0.2mA			-0.5	V
Current Gain Bandwidth Product	f _T	V _{CE} = -10V , I _C =-0.5A		60		MHZ